

查询CP108供应商
PROCESS CP108
Schottky Rectifier
Schottky Barrier Rectifier Chip - 2.0 Amp

捷多邦，专业PCB打样工厂，24小时加急出货™

Central
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	52 X 52 MILS
Die Thickness	9 MILS
Anode Bonding Pad Area	47 X 47 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 10,000Å

GEOMETRY



BACKSIDE CATHODE R0

GROSS DIE PER 4 INCH WAFER

5,110

PRINCIPAL DEVICE TYPES

1N5817

1N5818

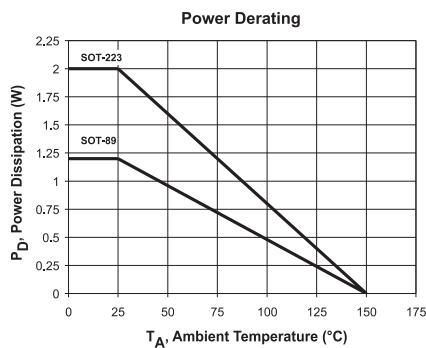
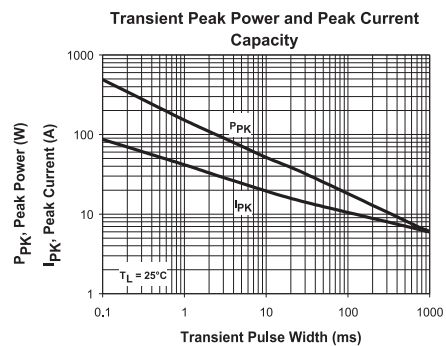
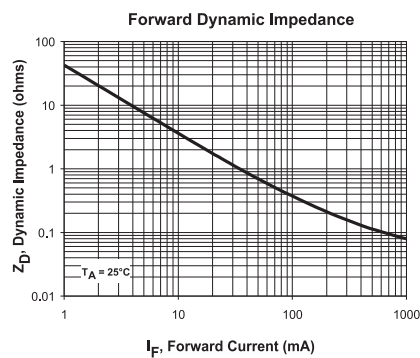
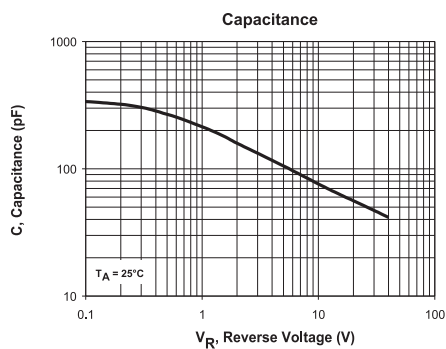
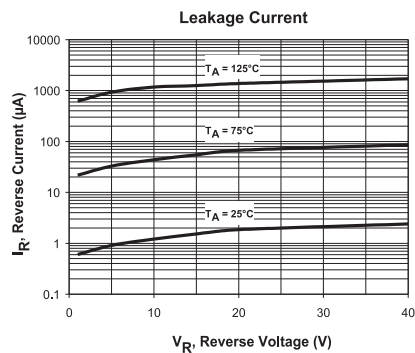
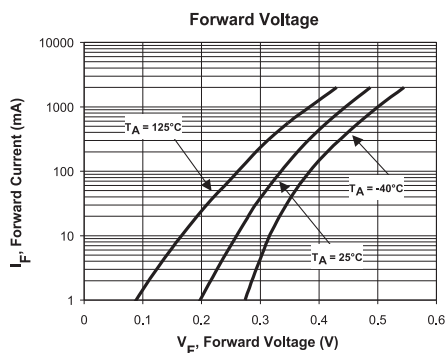
1N5819

CXSH-4

CZSH-4

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R8 (9 -September 2003)



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